SEMICONDUCTOR TECHNICAL DATA

GR3A ~ GR3M

SURFACE MOUNT FAST SWITCHING RECTIFIER Reverse Voltage 50~1000V, Forward Current 3 Ampere Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- For surface mount applications
- Low profile package
- Built-in strain relief, ideal for automated placement
- Fast switching for high efficiency
- Easy pick and place
- Glass passivated chip junction
- High temperature soldering:
 250 ℃/10 seconds at terminals

Mechanical Data

• Case: SMC molded plastic body over passivated chip

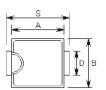
• Terminals: Solder plated, solderable per

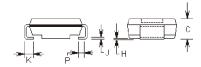
MIL-STD-750, method 2026

• Polarity: Color band denotes cathode end

Mounting Position: AnyWeight: 0.007 ounce, 0.25 gram







		DIMEN	SIONS		
DIM	inches		m	Note	
	M in .	Max.	M in .	Max.	NOTE
Α	0.260	0.280	6.60	7.11	
В	0.220	0.240	5.59	6.10	
С	0.075	0.095	1.90	2 .4 1	
D	0.115	0.121	2.92	3.07	
н	0.0020	0.0060	0.051	0.152	
J	0.006	0.012	0.15	0.30	
К	0.030	0.050	0.76	1 .2 7	
Р	0.020 REF		0.51		
s	0.305	0.320	7.75	8.13	

Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

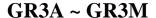
	Symbols	GR3A	GR3B	GR3D	GR3G	GR3J	GR3K	GR3M	Units
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum average forward rectified current at $\rm T_L = 75^{\circ}C$	I _(AV)	3.0							Amps
Peak forward surge current 8.3mS single half sine-wave superimposed on rated load (MIL-STD-750D 4066 method) T_=75 $^\circ\!\mathrm{C}$	I _{FSM}	100.0							Amps
Maximum instantaneous forward voltage at 3.0A	V _F	1.30							Volts
Maximum DC reverse current at rated DC blocking voltage $T_A = 25^{\circ}C$	I _R	10.0 250.0							μА
Maximum reverse recovery time (Note 1)	T _m	150 250 500						00	nS
Typical junction capacitance (Note 2)	C _J	60.0							ρF
Typical thermal resistance (Note 3)	R _{⊕JA} R _{⊕JL}	15.0 50.0						°C/W	
Operating junction and storage temperature range	T _J , T _{STG}	-55 to +150						°C	

Notes:

- (1) Reverse recovery test conditions: $I_F = 0.5A$, $I_R = 1.0A$, $I_R = 0.25A$
- (2) Measured at 1.0MHz and applied reverse voltage of 4.0 volts

Revision No: 0

(3) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.3X0.3" (8.0X8.0mm) copper pad areas





RATINGS AND CHARACTERISTIC CURVES

